

Optical study of excitation and deexcitation of Tm in GaN quantum dots

Andreev T., Liem N.Q., Hori Y., Tanaka M., Oda O., Dang D.L.S.,
Daudin B., Gayral B.

CEA/CNRS/UJF Research Group Nanophysique et Semiconducteurs, DRFMC/SP2M/PSC CEA-Grenoble,
17 rue des Martyrs, 38054-Grenoble Cedex 9, France; Institute of Materials Science (IMS), Vietnamese
Academy of Science and Technology, 18 Hoang Quoc Viet-Cau Giay-Hanoi, Viet Nam; College of
Technology, Hanoi National University, 144 Xuan Thuy-Cau Giay-Hanoi, Viet Nam; NGK Insulators, LTD,
2-24 Sudacho, Mizuhoku, Nagoya, Japan; CEA/CNRS/UJF Research Group Nanophysique et
Semiconducteurs, Laboratoire Spectrométrie Physique (CNRS UMR5588), Université J. Fourier, Boîte
Postale 87, 38402 Saint Martin d'Hères, France; EADS Astrium GmbH, 81663 Munich, Germany

Abstract: We report on the optical properties of molecular beam epitaxy grown GaN quantum dots (QDs) doped with Tm. Under optical excitation above the fundamental energy of GaN QDs, the fundamental transition emission from the GaN QD host was not observed while bright emission from Tm³⁺ manifolds demonstrated the efficient energy transfer from the host to Tm³⁺ ions. The photoluminescence as a function of temperature was fast quenched for transition from the high-lying manifolds state but very stable for the blue one resulting from the D₂₁ → F₄₃ transition. Mechanisms for excitation to and deexcitation from Tm³⁺ ions are discussed. © 2006 The American Physical Society.

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Correspondence Address: Gayral, B.; CEA/CNRS/UJF Research Group Nanophysique et Semiconducteurs, DRFMC/SP2M/PSC CEA-Grenoble, 17 rue des Martyrs, 38054-Grenoble Cedex 9, France; email: bruno.gayral@cea.fr

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Authors with affiliations:

1. Andreev, T., CEA/CNRS/UJF Research Group Nanophysique et Semiconducteurs, DRFMC/SP2M/PSC CEA-Grenoble, 17

rue des Martyrs, 38054-Grenoble Cedex 9, France, EADS Astrium GmbH, 81663 Munich, Germany

2. Liem, N.Q., CEA/CNRS/UJF Research Group Nanophysique et Semiconducteurs, DRFMC/SP2M/PSC CEA-Grenoble, 17 rue des Martyrs, 38054-Grenoble Cedex 9, France, Institute of Materials Science (IMS), Vietnamese Academy of Science and Technology, 18 Hoang Quoc Viet-Cau Giay-Hanoi, Viet Nam, College of Technology, Hanoi National University, 144 Xuan Thuy-Cau Giay-Hanoi, Viet Nam
3. Hori, Y., CEA/CNRS/UJF Research Group Nanophysique et Semiconducteurs, DRFMC/SP2M/PSC CEA-Grenoble, 17 rue des Martyrs, 38054-Grenoble Cedex 9, France, NGK Insulators, LTD, 2-24 Sudacho, Mizuhoku, Nagoya, Japan
4. Tanaka, M., NGK Insulators, LTD, 2-24 Sudacho, Mizuhoku, Nagoya, Japan
5. Oda, O., NGK Insulators, LTD, 2-24 Sudacho, Mizuhoku, Nagoya, Japan
6. Dang, D.L.S., CEA/CNRS/UJF Research Group Nanophysique et Semiconducteurs, Laboratoire Spectrométrie Physique (CNRS UMR5588), Université J. Fourier, Boîte Postale 87, 38402 Saint Martin d'Hères, France
7. Daudin, B., CEA/CNRS/UJF Research Group Nanophysique et Semiconducteurs, DRFMC/SP2M/PSC CEA-Grenoble, 17 rue des Martyrs, 38054-Grenoble Cedex 9, France
8. Gayral, B., CEA/CNRS/UJF Research Group Nanophysique et Semiconducteurs, DRFMC/SP2M/PSC CEA-Grenoble, 17 rue des Martyrs, 38054-Grenoble Cedex 9, France

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